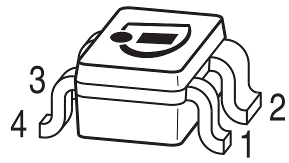
Low Noise Silicon Bipolar RF Transistor



- General purpose low noise amplifier for low voltage, low current applications
- High ESD robustness, typical 1500 V (HBM)
- Low minimum noise figure 1.1 dB at 1.8 GHz
- High linearity: output compression point OP1dB = 13 dBm @ 3 V, 35 mA, 1.8 GHz
- Pb-free (RoHS compliant) and halogen-free package with visible leads
- Qualification report according to AEC-Q101 available

ESD (**E**lectro**s**tatic **d**ischarge) sensitive device, observe handling precaution!

Type	Marking	Pin Configuration						Package
BFP460	ABs	1 = E	2 = C	3 = E	4=B	-	-	SOT343

Maximum Ratings at T_A = 25 °C, unless otherwise specified

Parameter	Symbol	Value	Unit
Collector-emitter voltage	V_{CEO}		V
T_A = 25 °C		4.5	
T_A = -55 °C		4.2	
Collector-emitter voltage	V_{CES}	15	
Collector-base voltage	V_{CBO}	15	
Emitter-base voltage	V_{EBO}	1.5	
Collector current	I_C	70	mA
Base current	I_B	7	
Total power dissipation[1)] $T_S \leq 92$°C	P_{tot}	230	mW
Junction temperature	T_J	150	°C
Ambient temperature	T_A	-65 ... 150	
Storage temperature	T_{Stg}	-65 ... 150	

[1] T_S is measured on the collector lead at the soldering point to the pcb

2013-09-13

Thermal Resistance

Parameter	Symbol	Value	Unit
Junction - soldering point[1)]	R_{thJS}	250	K/W

Electrical Characteristics at T_A = 25 °C, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
DC Characteristics					
Collector-emitter breakdown voltage I_C = 1 mA, I_B = 0	$V_{(BR)CEO}$	4.5	5.8	-	V
Collector-emitter cutoff current	I_{CES}				nA
V_{CE} = 15 V, V_{BE} = 0		-	-	1000	
V_{CE} = 2 V, V_{BE} = 0		-	1	30	
V_{CE} = 5 V, V_{BE} = 0 , T_A = 85°C Verified by random sampling		-	2	40	
Collector-base cutoff current	I_{CBO}				
V_{CB} = 2 V, I_E = 0		-	1	30	
V_{CB} = 5 V, I_E = 0		-	-	30	
Emitter-base cutoff current V_{EB} = 0,5 V, I_C = 0	I_{EBO}	-	1	500	
DC current gain V_{CE} = 3 V, I_C = 20 mA , pulse measured	h_{FE}	90	120	160	-

[1]For the definition of R_{thJS} please refer to Application Note AN077 (Thermal Resistance Calculation)

Electrical Characteristics at T_A = 25 °C, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
AC Characteristics (verified by random sampling)					
Transition frequency I_C = 30 mA, V_{CE} = 3 V, f = 1 GHz	f_T	16	22	-	GHz
Collector-base capacitance V_{CB} = 3 V, f = 1 MHz, V_{BE} = 0 , emitter grounded	C_{cb}	-	0.32	0.45	pF
Collector emitter capacitance V_{CE} = 3 V, f = 1 MHz, V_{BE} = 0 , base grounded	C_{ce}	-	0.28	-	
Emitter-base capacitance V_{EB} = 0.5 V, f = 1 MHz, V_{CB} = 0 , collector grounded	C_{eb}	-	0.55	-	
Minimum noise figure	NF_{min}				dB
V_{CE} = 2V, I_C = 3 mA , Z_S = $Z_{Sopt,}$ f = 100 MHz		-	0.7	-	
V_{CE} = 3V, I_C = 5 mA , Z_S = $Z_{Sopt,}$ f = 1.8 GHz		-	1.1	-	
V_{CE} = 3V, I_C = 5 mA , Z_S = $Z_{Sopt,}$ f = 3 GHz		-	1.2	-	

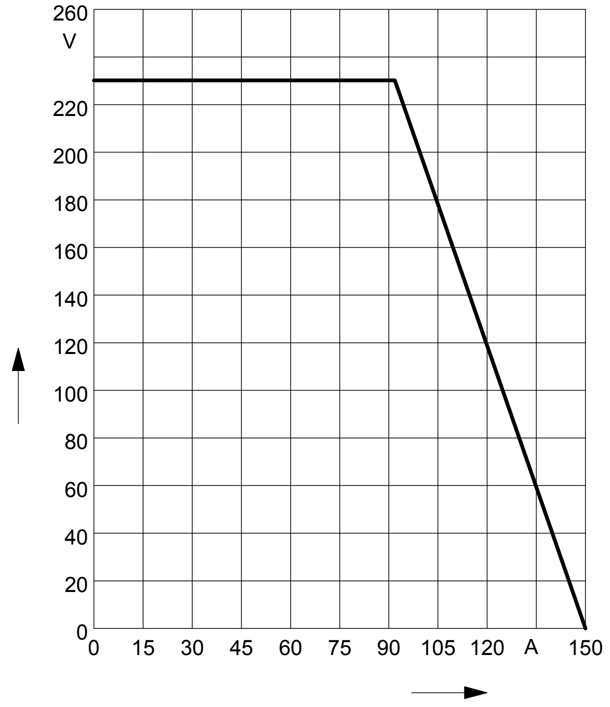
Electrical Characteristics at T_A = 25 °C, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
AC Characteristics (verified by random sampling)					
Maximum power Gain[1]	G_{max}				dB
I_C = 3 mA, V_{CE} = 1.5 V, $Z_S = Z_{Sopt}$, $Z_L = Z_{Lopt}$, f = 100 MHz		-	26.5	-	
I_C = 20 mA, V_{CE} = 3 V, $Z_S = Z_{Sopt}$, $Z_L = Z_{Lopt}$, f = 1,8 GHz		-	17.5	-	
f = 3 GHz		-	12.5	-	
Transducer gain	$\|S_{21e}\|^2$				dB
I_C = 3 mA, V_{CE} = 1.5 V, $Z_S = Z_L$ = 50Ω, f = 100 MHz		-	20	-	
I_C = 20 mA, V_{CE} = 3 V, $Z_S = Z_L$ = 50Ω , f = 1.8 GHz		-	15	-	
f = 3 GHz		-	10.5	-	
Third order intercept point at output[2]	$IP3$				dBm
V_{CE} = 3 V, I_C = 20 mA, f = 100 MHz		-	23.5	-	
V_{CE} = 3 V, I_C = 20 mA, f = 1.8 GHz		-	27.5	-	
1dB compression point at output	P_{-1dB}				
V_{CE} = 3V, I_C = 20mA , $Z_S=Z_L$ = 50Ω, f = 100 MHz		-	9.5	-	
V_{CE} = 3V, I_C = 20mA, $Z_S=Z_L$ = 50Ω, f = 1.8 GHz		-	11.5	-	
V_{CE} = 3V, I_C = 35mA, $Z_S=Z_L$ = 50Ω, f = 1.8 GHz		-	13	-	

[1] $G_{ma} = |S_{21} / S_{12}| (k-(k^2-1)^{1/2})$, $G_{ms} = |S_{21} / S_{12}|$

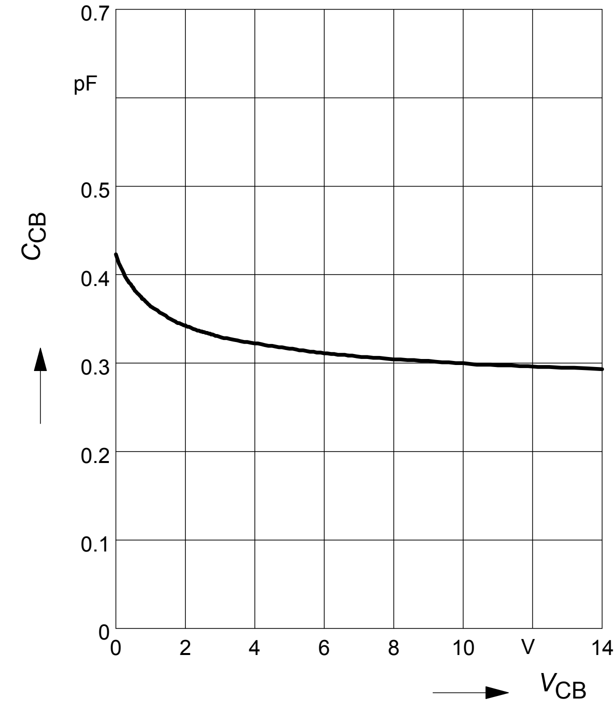
[2] IP3 value depends on termination of all intermodulation frequency components. Termination used for this measurement is 50Ω from 0.1 MHz to 6 GHz

Total power dissipation $P_{tot} = f(T_S)$



Collector-base capacitance $C_{cb} = f(V_{CB})$

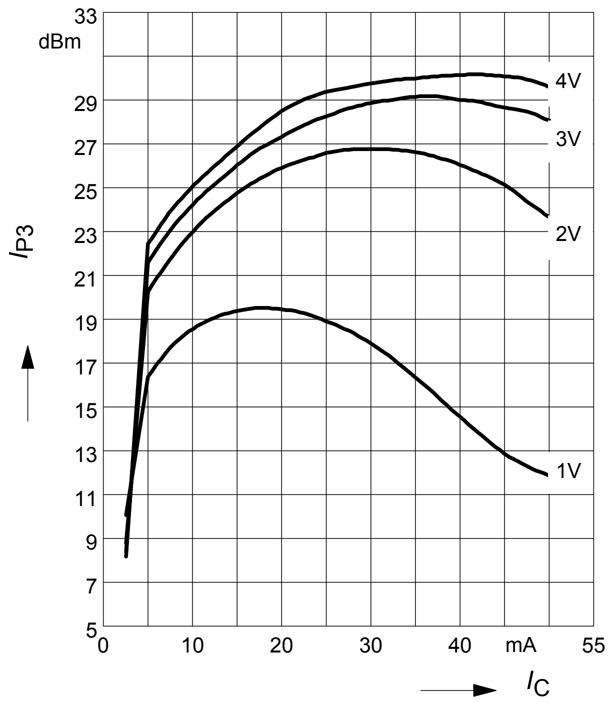
f = 1MHz



Third order Intercept Point $IP3 = f(I_C)$

(Output, $Z_S = Z_L = 50\Omega$)

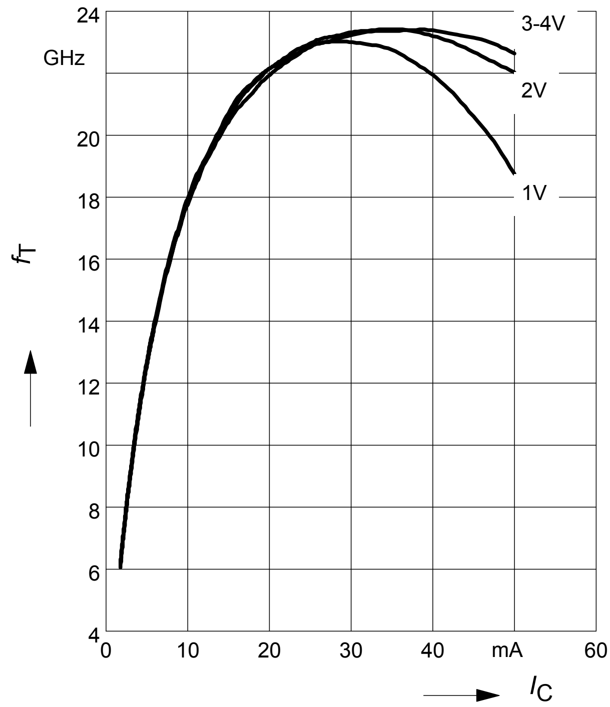
V_{CE} = parameter, f = 1800 MHz



Transition frequency $f_T = f(I_C)$

f = 1 GHz

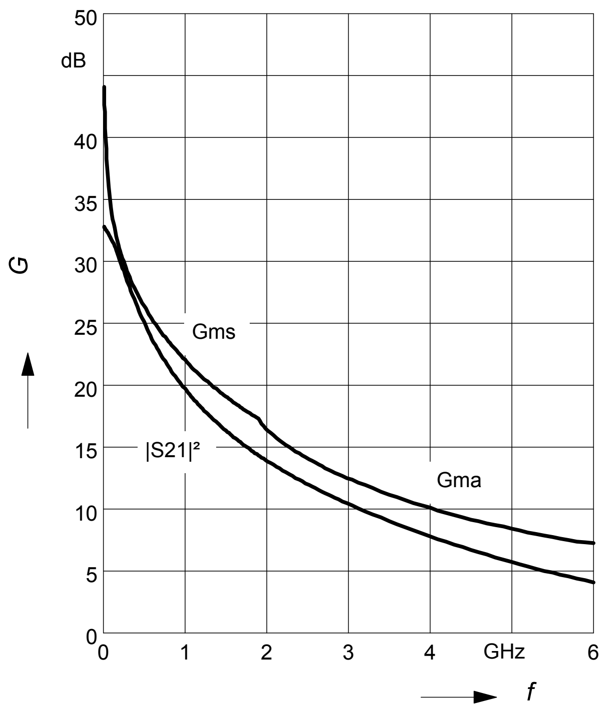
V_{CE} = parameter



2013-09-13

Power gain G_{ma}, G_{ms}, $|S_{21}|^2 = f\,(f)$

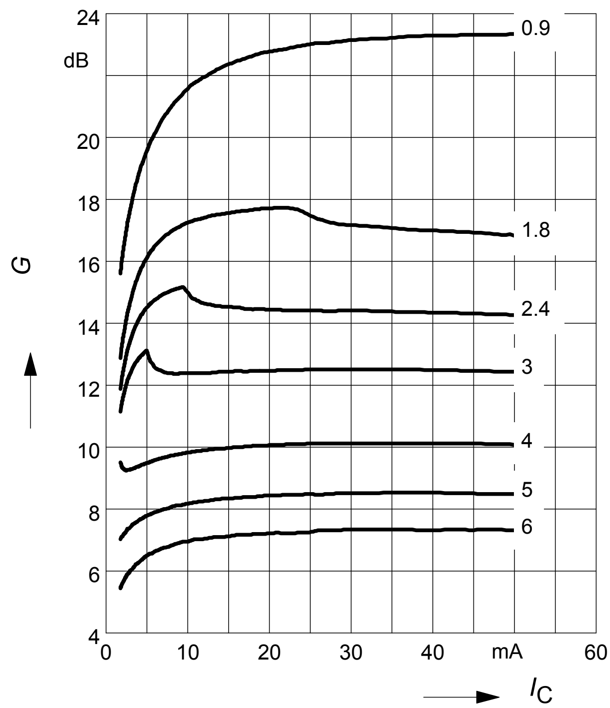
V_{CE} = 3 V, I_C = 20 mA



Power gain G_{ma}, G_{ms} = $f\,(I_C)$

V_{CE} = 3V

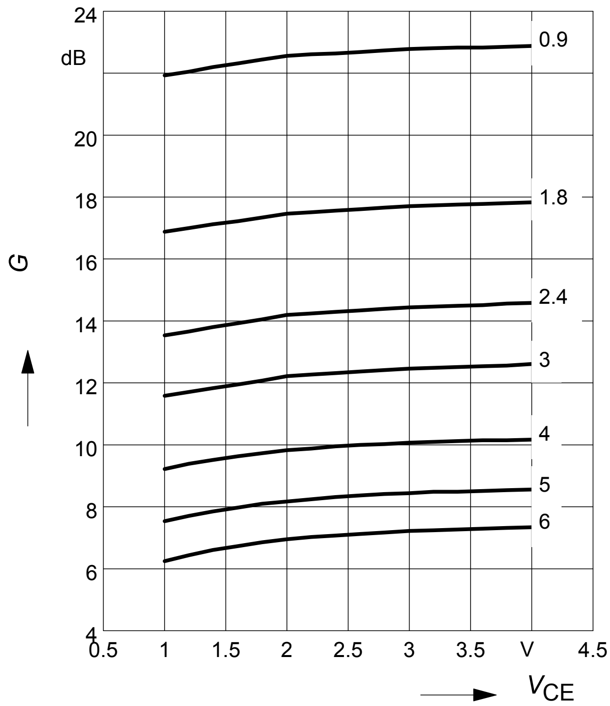
f = parameter in GHz



Power gain G_{ma}, G_{ms} = $f\,(V_{CE})$

I_C = 20 mA

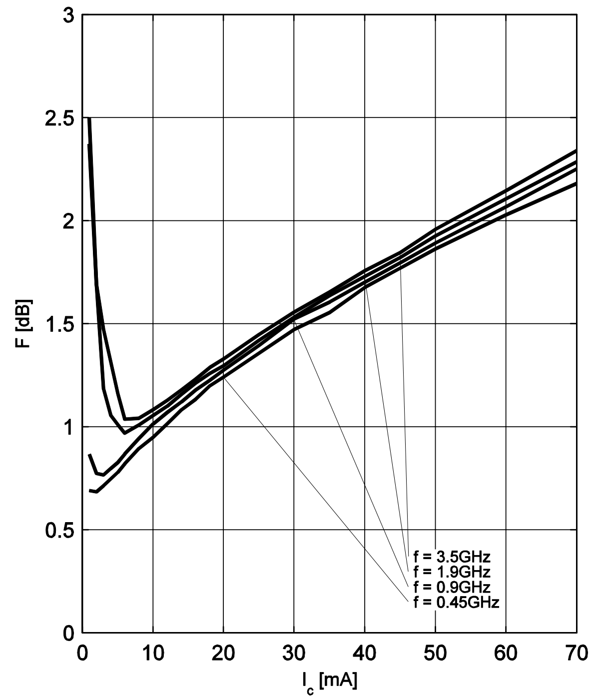
f = parameter in GHz



Noise figure F = $f(I_C)$

V_{CE} = 2 V, f = parameter

$Z_S = Z_{Sopt}$

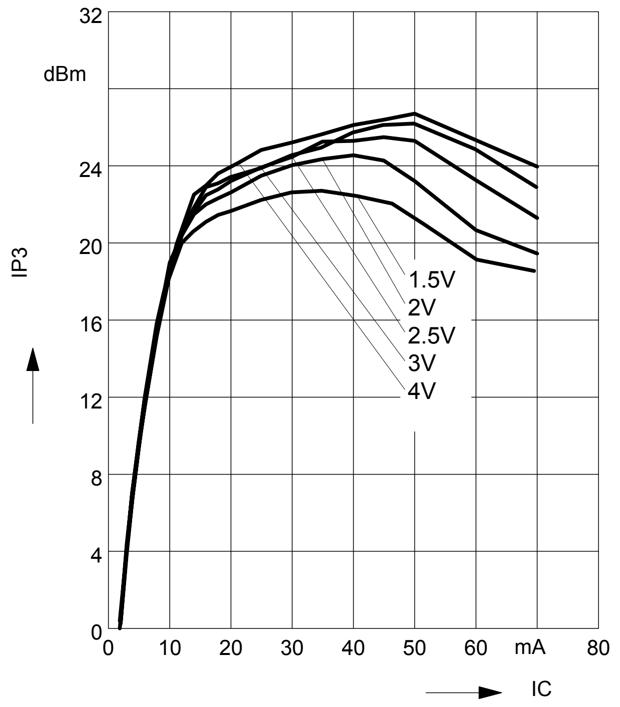


2013-09-13

Third order Intercept Point $IP_3 = f(I_C)$

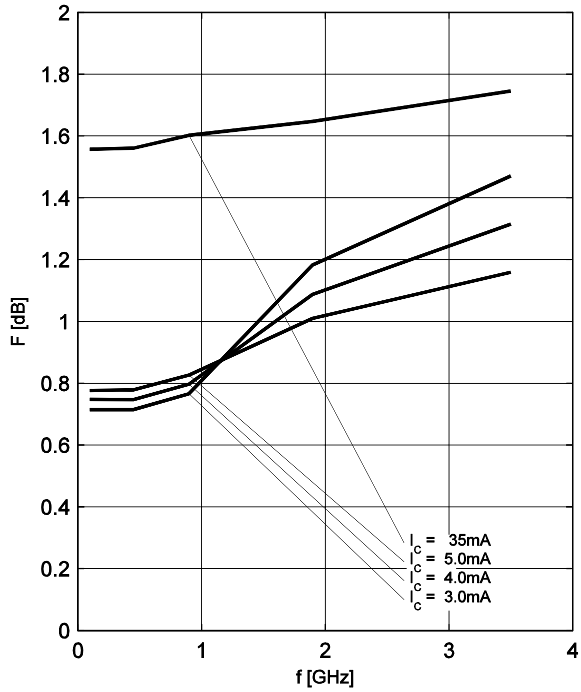
(Output, $Z_S = Z_L = 50\Omega$)

V_{CE} = parameter, f = 100MHz



Noise figure $F = f(f)$

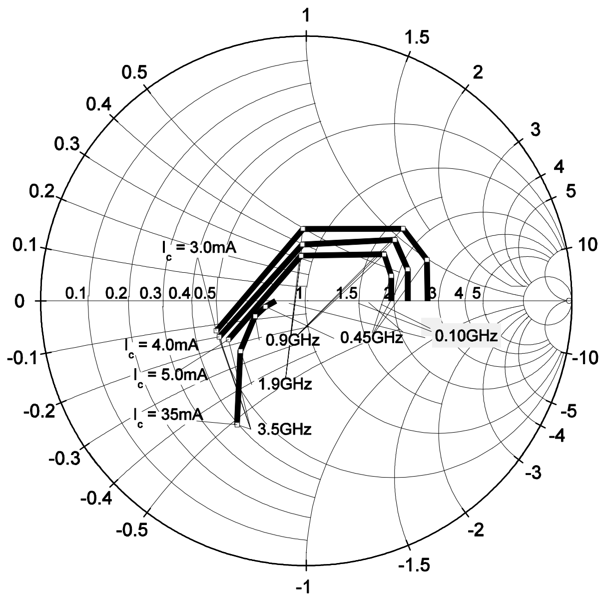
V_{CE} = 2V, $Z_S = Z_{Sopt}$, I_C = parameter



Source impedance for min.

noise figure vs. frequency

V_{CE} = 2V, I_C = parameter

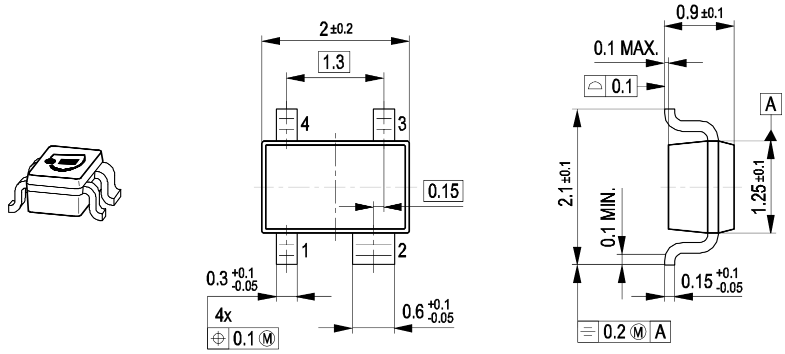


2013-09-13

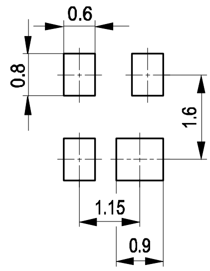
SPICE GP Model

For the SPICE Gummel Poon (GP) model as well as for the S-parameters (including noise parameters) please refer to our internet website www.infineon.com/rf.models.
Please consult our website and download the latest versions before actually starting your design. You find the BFP460 SPICE GP model in the internet in MWO- and ADS-format, which you can import into these circuit simulation tools very quickly and conveniently. The model already contains the package parasitics and is ready to use for DC and high frequency simulations. The terminals of the model circuit correspond to the pin configuration of the device. The model parameters have been extracted and verified up to 6 GHz using typical devices. The BFP460 SPICE GP model reflects the typical DC- and RF-performance within the limitations which are given by the SPICE GP model itself. Besides the DC characteristics all S-parameters in magnitude and phase, as well as noise figure (including optimum source impedance, equivalent noise resistance and flicker noise) and intermodulation have been extracted.

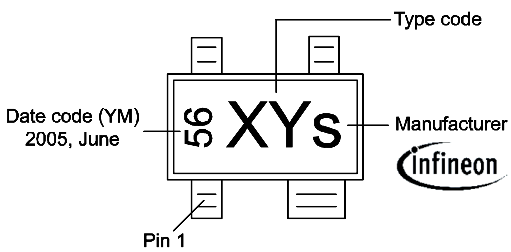
Package Outline



Foot Print

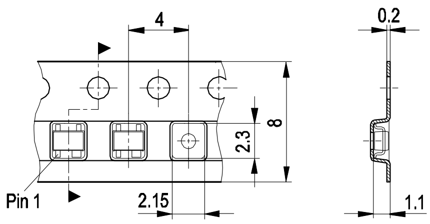


Marking Layout (Example)



Standard Packing

Reel ø180 mm = 3.000 Pieces/Reel
Reel ø330 mm = 10.000 Pieces/Reel



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